

FEATURES

- Magnetically shielded and molded type inductor, possible to decrease noise.
- Very high DC saturation current.
- Low core loss and very low DC resistance.
- Molded construction to be excellent identically performance and machanical strength.
- Suitable for surface mount equipment.

APPLICATIONS

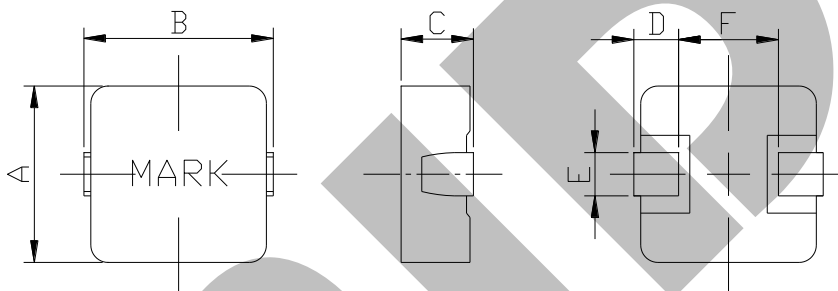
- Suitable as circuit for digital amp, Motherboard for panel computer and notebook computer DC/DC converter, etc.

特 征

- 磁屏蔽一体成型电感，可有效防止噪音；
- 超高饱和电流；
- 低损耗及超低直流电阻。
- 一体成型结构具优秀一致性和机械强度。
- 适合表面贴装。

用 途

- 适用于数字功放电路，平板电脑及笔记本电脑主板及显卡 DC/DC 转换器等。

SHAPES AND DIMENSIONS (mm)

TYPE	A	B	C(Max)	D(Ref.)	E(Ref.)	F(Ref.)
HPB0603-	6.60±0.5	7.30±0.5	3.50	1.8	3.0	3.0
HPB0604-	6.60±0.5	7.30±0.5	4.20	1.8	3.0	3.0
HPB1003-	10.00±0.5	11.20±0.5	3.70	2.3	3.0	6.5
HPB1004-	10.00±0.5	11.20±0.5	4.20	2.3	3.0	6.5
HPB1005-	10.00±0.5	11.20±0.5	5.00	2.3	3.0	6.5
HPB1203-	12.80±0.5	13.60±0.5	3.80	3.0	3.8	7.5
HPB1204-	12.80±0.5	13.60±0.5	4.50	3.0	3.8	7.5
HPB1205-	12.80±0.5	13.60±0.5	5.50	3.0	3.8	7.5
HPB1206-	12.80±0.5	13.60±0.5	6.30	3.0	3.8	7.5

HPB0603-SERIES

P/N	L(uH)	DCR(mΩ)		Idc	Isat
	Inductance	DC Resistance		Temperature rise current	Inductance decrease current
	± 20%	Typ	Max	Max	Max
R10M	0.10	1.5	1.7	33	60
R15M	0.15	1.9	2.5	28	52
R20M	0.20	2.4	2.8	25	41
R22M	0.22	2.5	3.0	22	40
R33M	0.33	3.5	4.0	20	30
R47M	0.47	4.0	4.5	18	27
R56M	0.56	4.3	5.0	16	25
R68M	0.68	5.0	5.5	15	24
R82M	0.82	6.7	8.0	13	23
1R0M	1.00	8.3	10.0	11	22
1R2M	1.20	9.0	12.0	10	20
1R5M	1.50	14.0	15.0	9	18
2R2M	2.20	18.0	20.0	8	15
2R7M	2.70	23.0	25.0	7	14
3R3M	3.30	28.0	30.0	6	13
4R7M	4.70	37.0	40.0	5.5	10
6R8M	6.80	54.0	60.0	4.5	8
8R2M	8.20	64.0	70.0	4.0	7.5
100M	10.0	102.0	120	3.0	7
150M	15.0	125.0	150	2.0	4

HPB0604-SERIES

P/N	L(uH)	DCR(mΩ)		Idc	Isat
	Inductance	DC Resistance		Temperature rise current	Inductance decrease current
	± 20%	Typ	Max	Max	Max
R33M	0.33	2.5	3.0	24	35
R56M	0.56	3.2	4.0	20	30
1R0M	1.0	7.5	10.0	15	20
4R7M	4.7	32	40.0	6	11
220M	2.2	165	180	0.8	1.5

SMD MOLDING POWER INDUCTORS 一体成型贴片功率电感

HPB 系列

HPB1003-SERIES

P/N	L(uH)	DCR(mΩ)		Idc	Isat
	Inductance	DC Resistance		Temperature rise current	Inductance decrease current
	± 20%	Typ	Max	Max	Max
R56M	0.56	1.5	2.0	20	35
5R6M	5.6	22.0	25.0	7	14

HPB1004-SERIES

P/N	L(uH)	DCR(mΩ)		Idc	Isat
	Inductance	DC Resistance		Temperature rise current	Inductance decrease current
	± 20%	Typ	Max	Max	Max
R18M	0.18	0.88	1.0	40	60
R33M	0.33	1.1	1.3	35	55
R47M	0.47	1.2	1.4	30	52
R56M	0.56	1.7	1.9	28	50
R68M	0.68	1.8	2.0	20	32
1R0M	1.0	3.7	4.2	18	35
1R5M	1.5	5.3	5.5	15	28
2R2M	2.2	8.2	9.0	12	26
3R3M	3.3	10	12	10	19
3R9M	3.9	11	13	10	18
4R7M	4.7	15	17	9.5	17
5R6M	5.6	18	20	8.5	16
6R8M	6.8	21	24	8.0	14
8R2M	8.2	31	35	7.0	13
100M	10.0	33	36	6.8	12
150M	15.0	43	48	5.0	6

HPB1005-SERIES

P/N	L(uH)	DCR(mΩ)		Idc	Isat
	Inductance	DC Resistance		Temperature rise current	Inductance decrease current
	± 20%	Typ	Max	Max	Max
R33M	0.56	1.1	1.3	33	52
R56M	0.56	1.6	1.9	28	50

HPB1203-SERIES

P/N	L(μ H)	DCR($m\Omega$)		Idc	Isat
	Inductance	DC Resistance		Temperature rise current	Inductance decrease current
	$\pm 20\%$	Typ	Max	Max	Max
R10M	0.10	0.8	1.0	43	84
R15M	0.15	1.0	1.2	41	75
R22M	0.22	1.1	1.3	39	65
R33M	0.33	1.3	1.5	36	62
R47M	0.47	1.6	2.0	32	55
R60M	0.60	1.8	2.2	29	51
R68M	0.68	2.3	2.5	28	49
R82M	0.82	2.6	3.0	25	44
1R0M	1.00	3.3	3.5	24	40
1R5M	1.50	5.1	5.5	19	35
2R2M	2.20	7.2	8.0	16	30
3R3M	3.30	11.0	12	12	27
4R7M	4.70	14.3	15	10	24
6R8M	6.80	19.8	22	9	18
8R2M	8.20	24.8	28	8	16
100M	10.0	30.4	34	7	14

HPB1204-SERIES

P/N	L(μ H)	DCR($m\Omega$)		Idc	Isat
	Inductance	DC Resistance		Temperature rise current	Inductance decrease current
	$\pm 20\%$	Typ	Max	Max	Max
R10M	0.10	0.9	1.1	43	75
R22M	0.22	1.2	1.4	41	70
R33M	0.33	1.3	1.5	38	60
R47M	0.47	1.4	1.8	32	55
R60M	0.60	2.0	2.5	30	50
R68M	0.68	2.1	2.6	28	46
R82M	0.82	2.7	3.2	3.1	44
1R0M	1.00	3.0	3.5	24	40
1R5M	1.50	5.5	6.0	18	30
2R2M	2.20	6.4	7.0	16	22
3R3M	3.30	7.5	8.5	14	20
4R7M	4.70	10.5	12.0	12	15

HPB1205-SERIES

P/N	L(uH)	DCR(mΩ)		Idc	Isat
	Inductance	DC Resistance		Temperature rise current	Inductance decrease current
	±20%	Typ	Max	Max	Max
R10M	0.10	0.53	0.60	55	118
R22M	0.22	0.64	0.80	51	110
R33M	0.33	0.85	1.10	42	80
R47M	0.47	1.10	1.30	38	65
R68M	0.68	1.50	1.80	34	54
R82M	0.82	2.00	2.30	31	53
1R0M	1.00	2.10	2.50	29	50
1R5M	1.50	3.40	4.10	23	48
2R2M	2.20	4.60	5.50	20	32
3R3M	3.30	7.70	10.0	15	30
4R7M	4.70	12.8	15.0	12	27
6R8M	6.80	15.5	20.0	11	21
8R2M	8.20	19.0	25.0	10	18
100M	10.0	21.5	28.0	9	16

HPB1206-SERIES

P/N	L(uH)	DCR(mΩ)		Idc	Isat
	Inductance	DC Resistance		Temperature rise current	Inductance decrease current
	±20%	Typ	Max	Max	Max
R10M	0.10	0.47	0.50	60	120
R33M	0.33	0.83	0.90	46	65
R47M	0.47	1.00	1.20	41	63
R56M	0.60	1.20	1.40	37	62
R68M	0.68	1.40	1.60	35	60
R82M	0.82	1.60	1.80	33	50
1R0M	1.00	1.70	2.00	32	49
1R5M	1.50	2.50	3.00	27	45
2R2M	2.20	3.50	4.50	22	40
3R3M	3.30	5.70	7.00	18	35
4R7M	4.70	9.30	12.0	14	30
6R8M	6.80	13.1	14.0	12	17
8R2M	8.20	14.5	16.0	11	16
100M	10.0	15.8	18.0	10	15